EMG2DXV5, EMG5DXV5

Dual Bias Resistor Transistors

NPN Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

This new series of digital transistors is designed to replace a single device and its external resistor bias network. The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base−emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space. The device is housed in the SOT−553 package which is designed for low power surface mount applications.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- Moisture Sensitivity Level: 1
- Available in 8 mm, 7 inch Tape and Reel
- Lead−Free Solder Plating
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation T_A = 25°C Derate above 25°C	P_D	230 (Note 1) 338 (Note 2) 1.8 (Note 1) 2.7 (Note 2)	mW °C/W
Thermal Resistance − Junction-to-Ambient	$R_{\theta JA}$	540 (Note 1) 370 (Note 2)	°C/W
Thermal Resistance − Junction-to-Lead	$R_{\theta JL}$	264 (Note 1) 287 (Note 2)	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR−4 @ Minimum Pad
2. FR−4 @ 1.0 x 1.0 inch Pad

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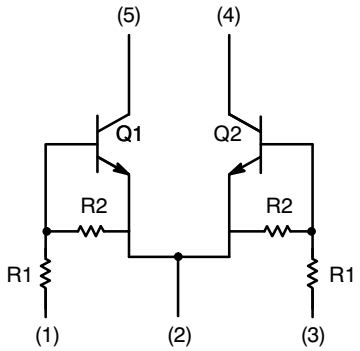
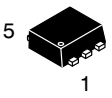
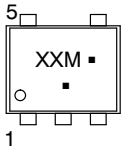
NPN SILICON BIAS RESISTOR TRANSISTORS





SOT−553
CASE 463B

MARKING DIAGRAM



XX = UF (EMG5)
UP (EMG2)
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

DEVICE MARKING AND RESISTOR VALUES

Device	Package	Marking	R1 (K)	R2 (K)
EMG2DXV5	SOT−553	UP	47	47
EMG5DXV5	SOT−553	UF	10	47

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS (Q1 & Q2)						
Collector-Base Cutoff Current (V_{CB} = 50 V, I_E = 0)		I_{CBO}	−	−	100	nAdc
Collector-Emitter Cutoff Current (V_{CE} = 50 V, I_B = 0)		I_{CEO}	−	−	500	nAdc
Emitter-Base Cutoff Current (V_{EB} = 6.0 V, I_C = 0)	EMG2DXV5 EMG5DXV5	I_{EBO}	− −	− −	0.1 0.2	mAdc
Collector-Base Breakdown Voltage (I_C = 10 μA, I_E = 0)		$V_{(BR)CBO}$	50	−	−	Vdc
Collector-Emitter Breakdown Voltage (Note 3) (I_C = 2.0 mA, I_B = 0)		$V_{(BR)CEO}$	50	−	−	Vdc
ON CHARACTERISTICS (Q1 & Q2) (Note 3)						
DC Current Gain (V_{CE} = 10 V, I_C = 5.0 mA)	EMG2DXV5 EMG5DXV5	h_{FE}	80 80	140 140	− −	
Collector-Emitter Saturation Voltage (IC = 10 mA, I_B = 0.3 mA)		$V_{CE(sat)}$	−	−	0.25	Vdc
Output Voltage (on) (V_{CC} = 5.0 V, V_B = 3.5 V, R_L = 1.0 kΩ) (V_{CC} = 5.0 V, V_B = 2.5 V, R_L = 1.0 kΩ)	 EMG2DXV5 EMG5DXV5	V_{OL}	 − −	 − −	 0.2 0.2	Vdc
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.5 V, R_L = 1.0 kΩ)		V_{OH}	4.9	−	−	Vdc
Input Resistor	EMG2DXV5 EMG5DXV5	R_1	32.9 7.0	47 10	61.1 13	kΩ
Resistor Ratio	EMG2DXV5 EMG5DXV5	R_1/R_2	0.8 0.17	1.0 0.21	1.2 0.25	

3. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%

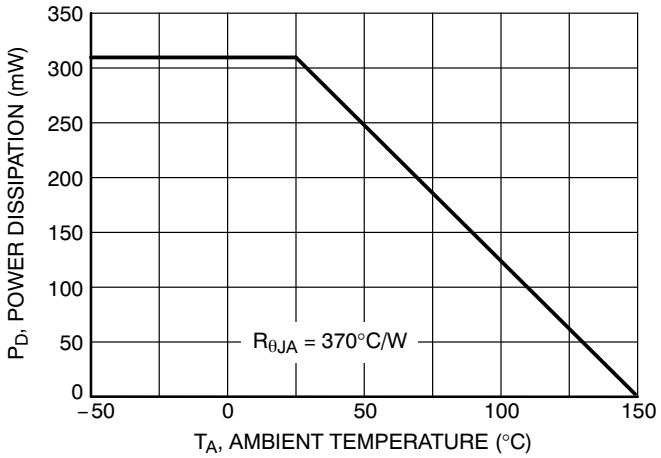


Figure 1. Derating Curve

TYPICAL ELECTRICAL CHARACTERISTICS — EMG2DXV5

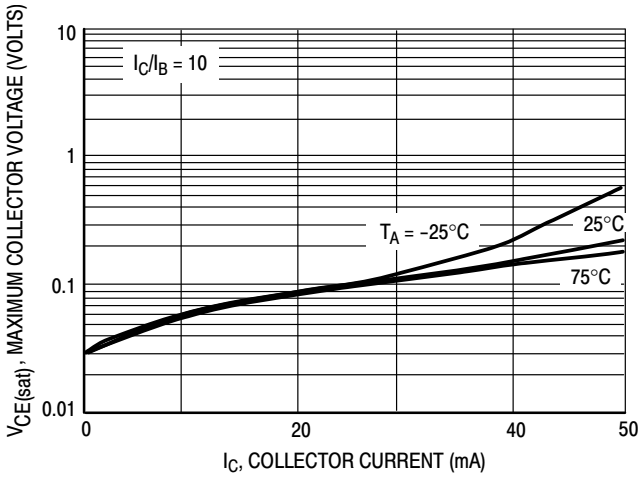


Figure 2. $V_{CE(sat)}$ versus I_C

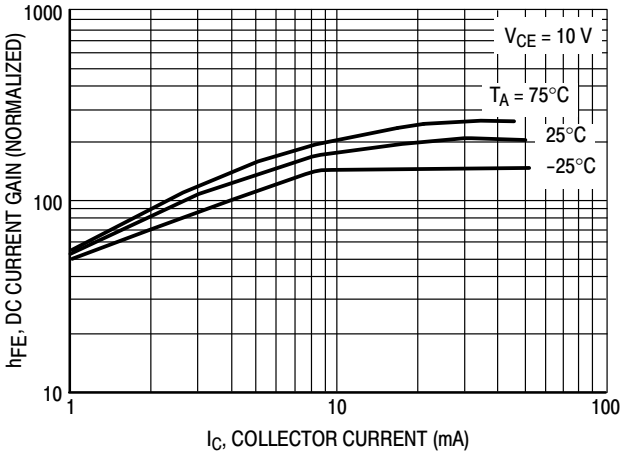


Figure 3. DC Current Gain

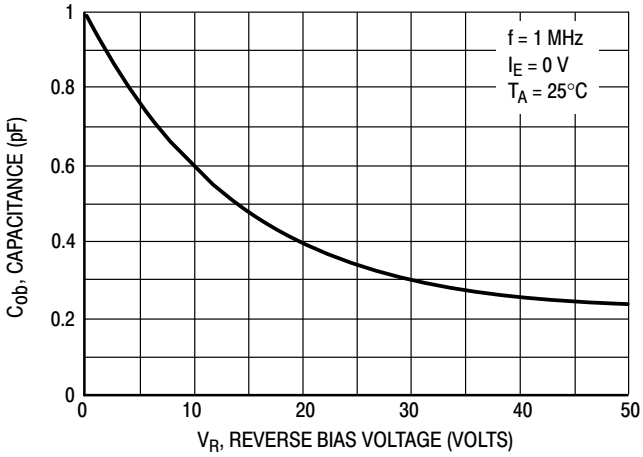


Figure 4. Output Capacitance

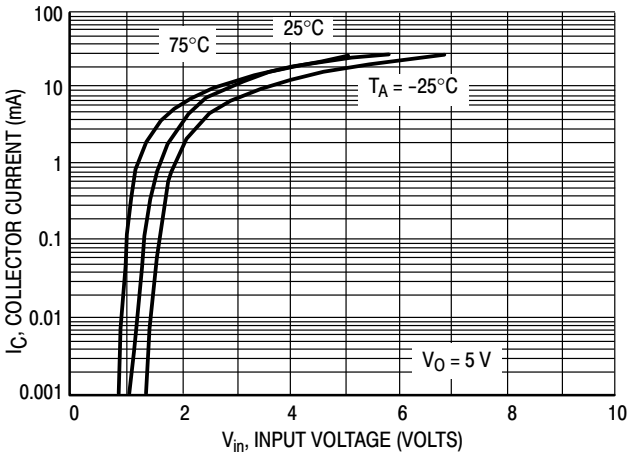


Figure 5. Output Current versus Input Voltage

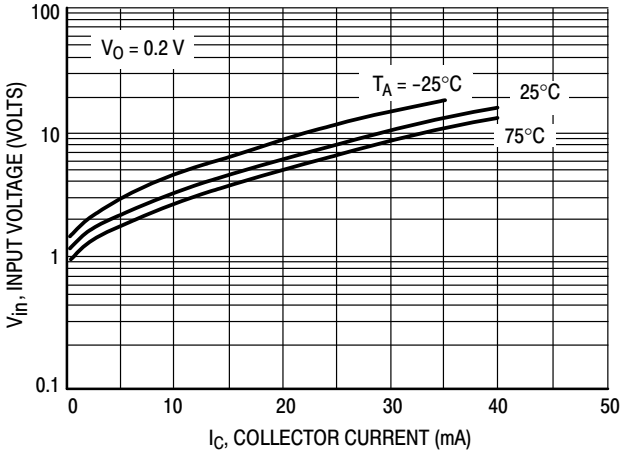


Figure 6. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS – EMG5DXV5

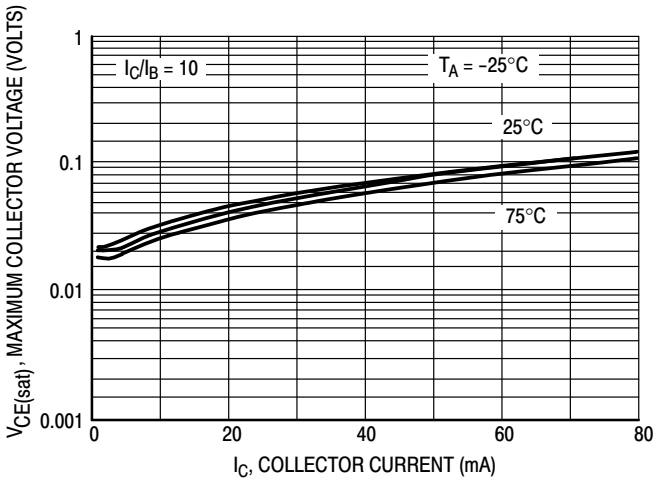


Figure 7. $V_{CE(sat)}$ versus I_C

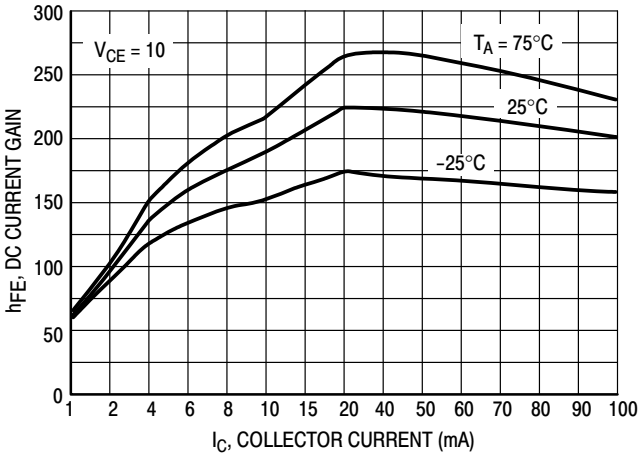


Figure 8. DC Current Gain

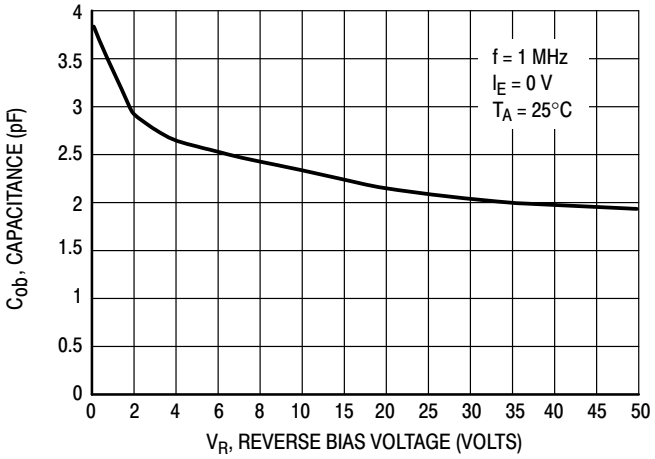


Figure 9. Output Capacitance

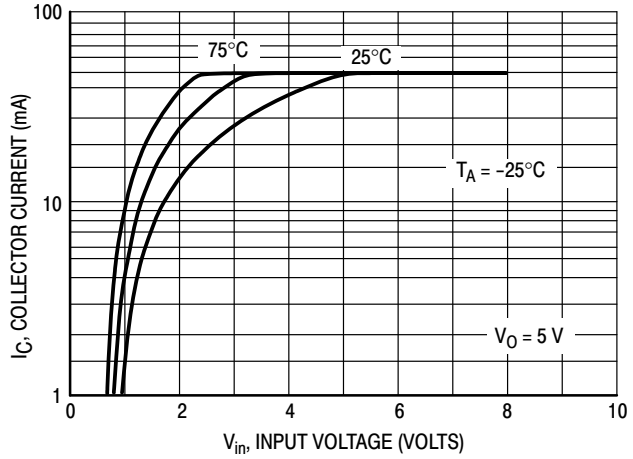


Figure 10. Output Current versus Input Voltage

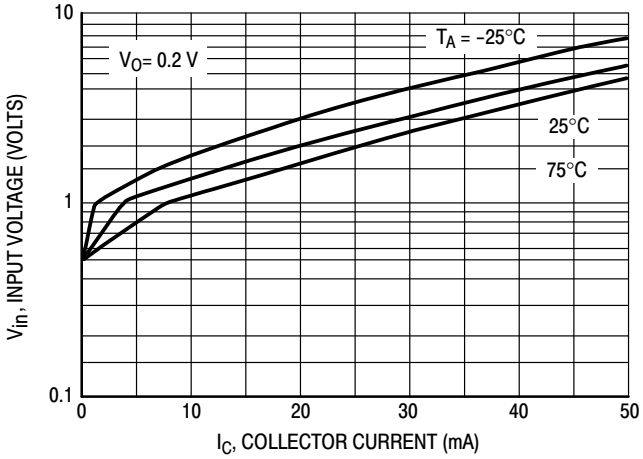


Figure 11. Input Voltage versus Output Current

TYPICAL APPLICATIONS FOR NPN BRTs

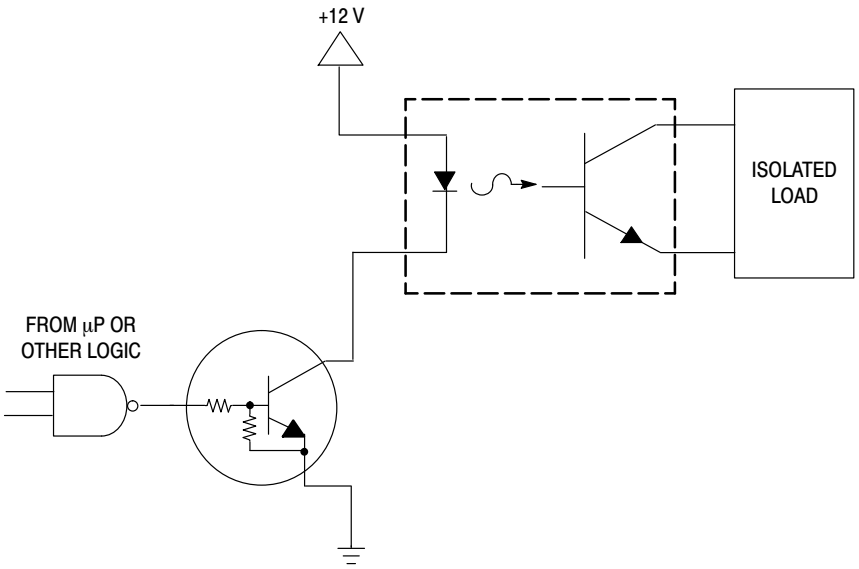


Figure 12. Level Shifter: Connects 12 or 24 Volt Circuits to Logic

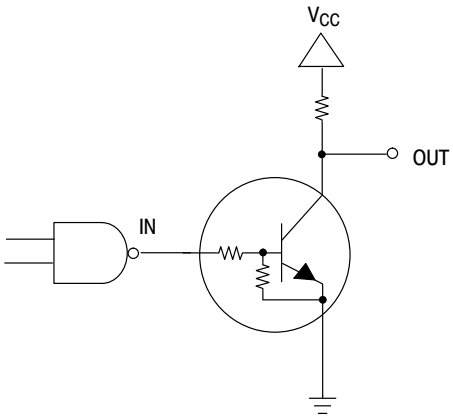


Figure 13. Open Collector Inverter: Inverts the Input Signal

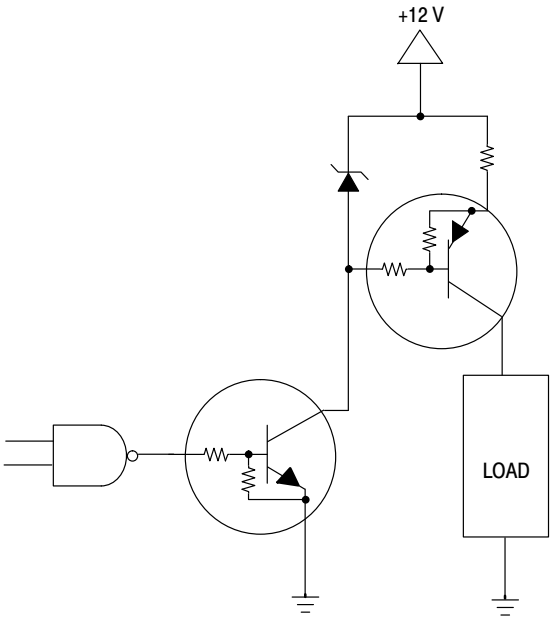


Figure 14. Inexpensive, Unregulated Current Source

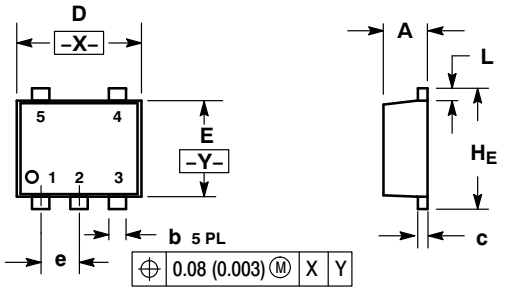
DEVICE ORDERING INFORMATION

Device	Package	Shipping†
EMG2DXV5T1G	SOT−553 (Pb−Free)	4000 / Tape & Reel
EMG2DXV5T5G	SOT−553 (Pb−Free)	8000 / Tape & Reel
EMG5DXV5T1G	SOT−553 (Pb−Free)	4000 / Tape & Reel
EMG5DXV5T5G	SOT−553 (Pb−Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

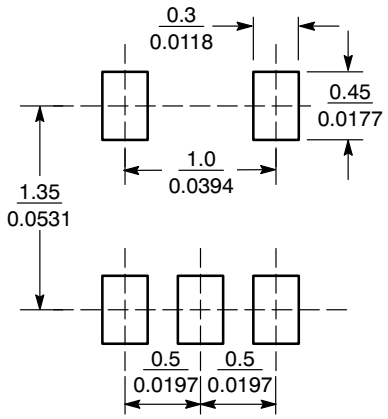
SOT−553
CASE 463B
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.022	0.024
b	0.17	0.22	0.27	0.007	0.009	0.011
c	0.08	0.13	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.063	0.067
E	1.10	1.20	1.30	0.043	0.047	0.051
e	0.50 BSC			0.020 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H_E	1.50	1.60	1.70	0.059	0.063	0.067

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
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Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
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Phone: 421 33 790 2910
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